Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = +25°C
60V	2Ω @ V_{GS} = 5.0V	340mA
	2.5Ω @ V_{GS} = 2.5V	300mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DIODES™ DMN61D9UWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications:

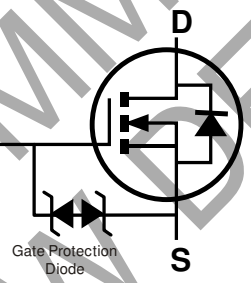
- Motor controls
- Power management functions
- Backlighting

Mechanical Data

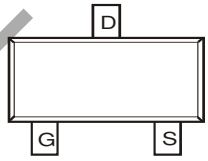
- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT323

Top View



Equivalent Circuit



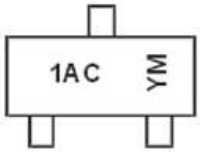
Top View

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN61D9UWQ-7	SOT323	3,000	Tape & Reel
DMN61D9UWQ-13	SOT323	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1AC= Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: J = 2022)
M = Month (ex: 9 = September)

Date Code Key

Year	2017	…	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	E	…	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 5.0V	Steady State	T_A = +25°C T_A = +70°C	I_D	340 270	mA
	t<5s	T_A = +25°C T_A = +70°C	I_D	400 300	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.4	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I_{DM}	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	393	°C/W
	t<5s		306	
Total Power Dissipation (Note 6)		P_D	440	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	289	°C/W
	t<5s		235	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	V_{DS} = 10V, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.2	2.0	Ω	V_{GS} = 5.0V, I_D = 0.05A
			1.6	2.5		V_{GS} = 2.5V, I_D = 0.05A
			2.5	3.5		V_{GS} = 1.8V, I_D = 0.05A
Forward Transconductance	$\|Y_{fs}\|$	200	—	—	mS	V_{DS} =10V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	—	0.75	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	28.5	—	pF	V_{DS} = 30V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	3.9	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.5	—	pF	
Gate Resistance	R_g	—	65	—	Ω	f = 1MHz, V_{GS} = 0V, V_{DS} = 0V
Total Gate Charge	Q_g	—	0.4	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.1	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	2.1	—	ns	V_{DD} = 30V, V_{GS} = 10V, R_G = 25Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	1.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	14.4	—	ns	
Turn-Off Fall Time	t_F	—	8.4	—	ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

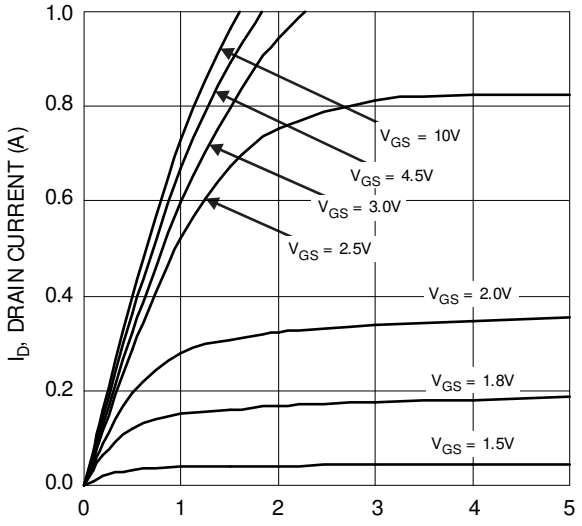


Figure 1 Typical Output Characteristics

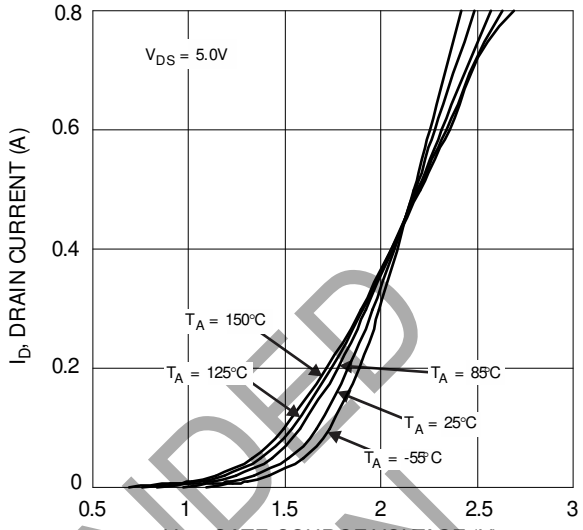


Figure 2 Typical Transfer Characteristics

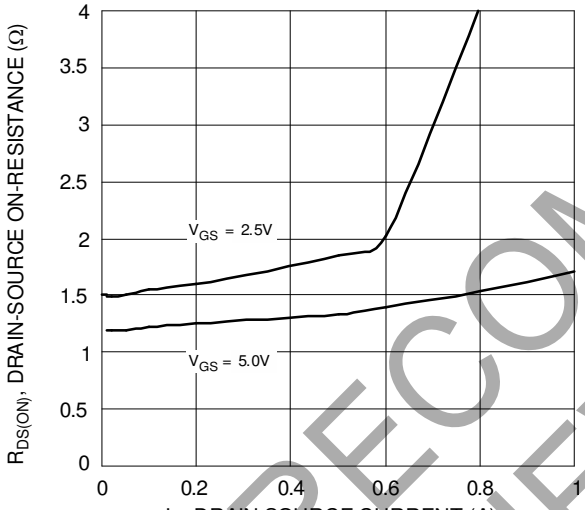


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

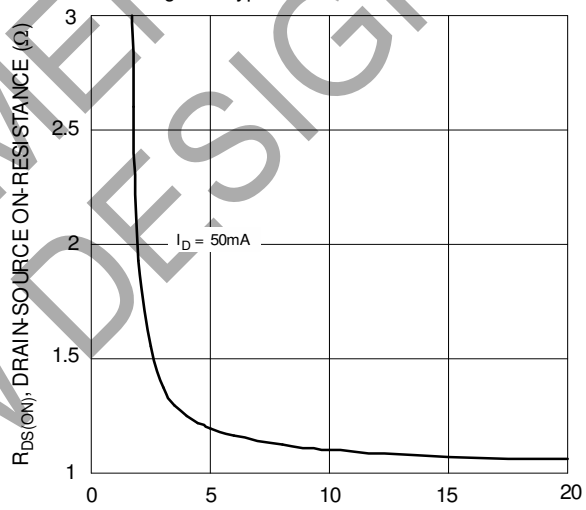


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

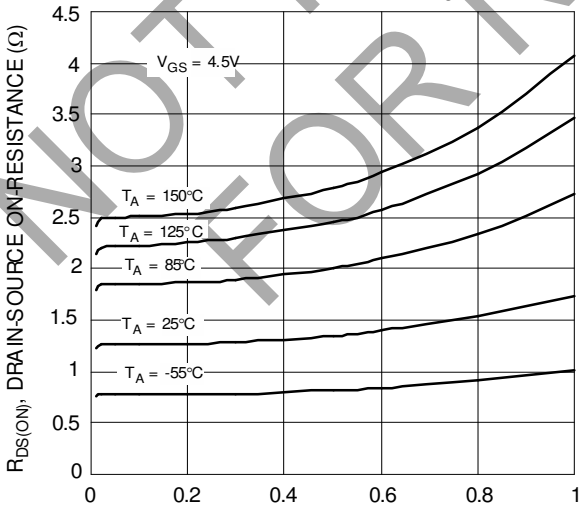


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

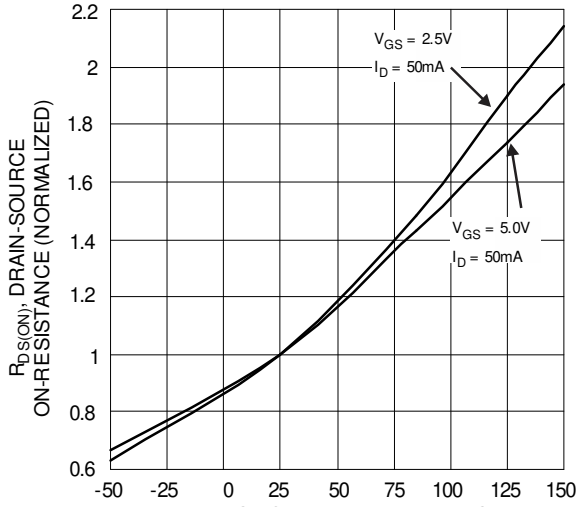


Figure 6 On-Resistance Variation with Junction Temperature

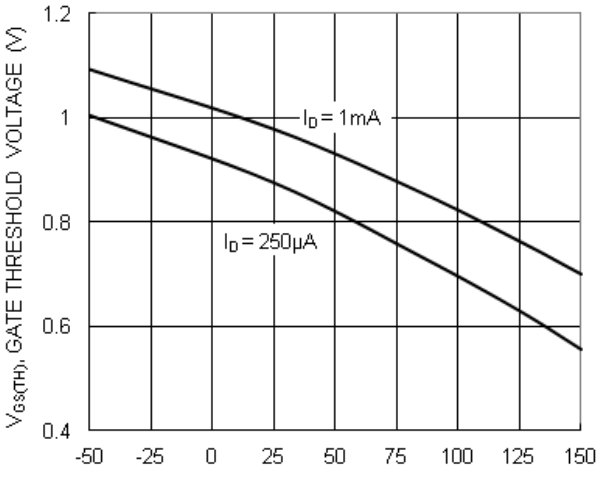


Figure 7. Gate Threshold Variation vs. Junction Temperature

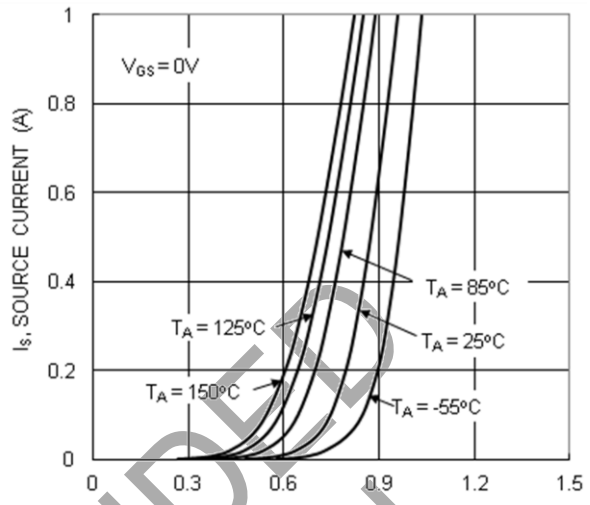


Figure 8. Diode Forward Voltage vs. Current

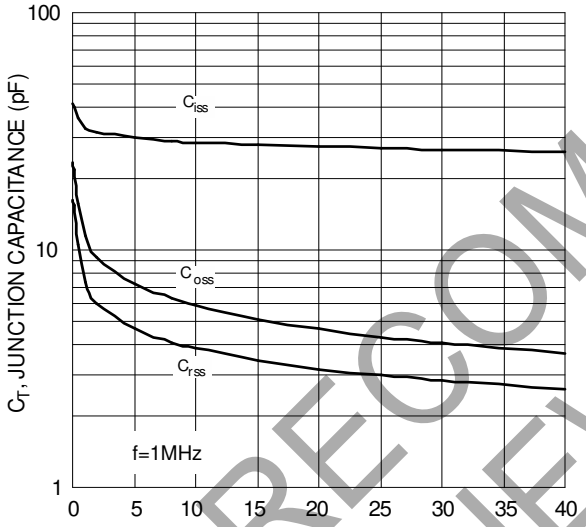


Figure 9 Typical Junction Capacitance

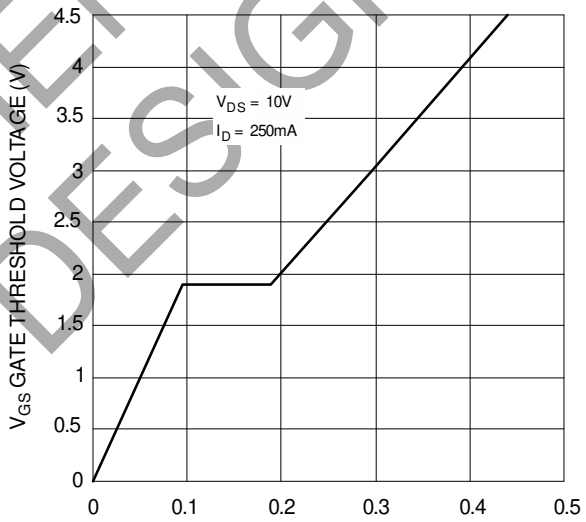


Figure 10 Gate Charge

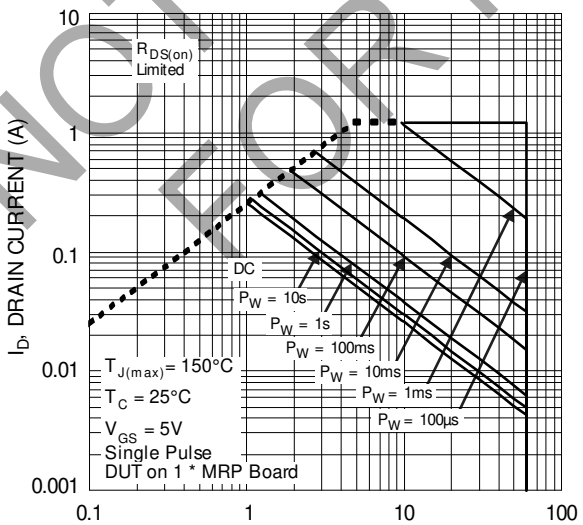


Figure 11 SOA, Safe Operation Area

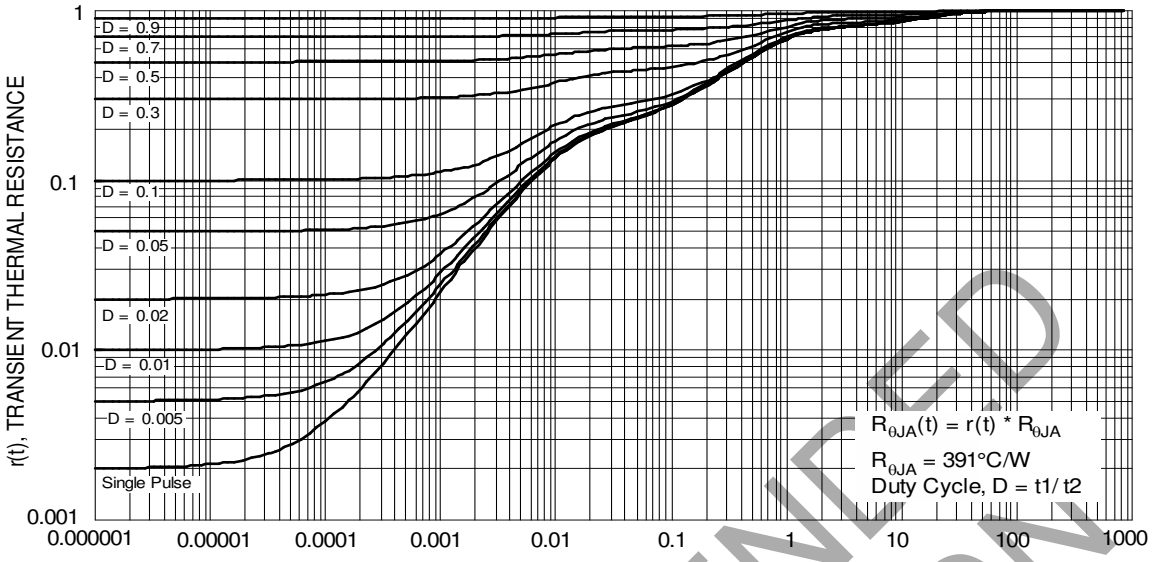
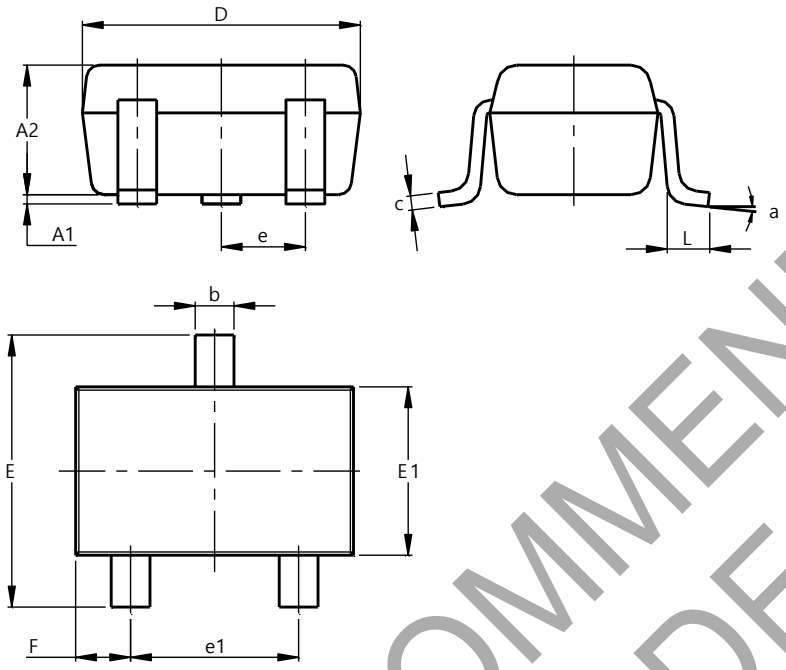


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

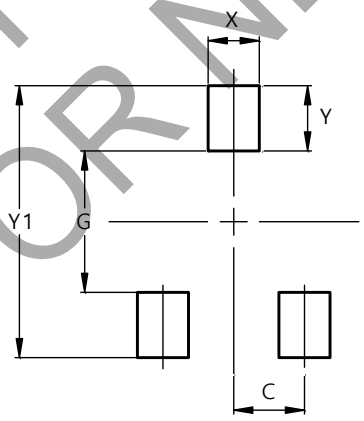


SOT323			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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